

Docket No.: 067161-0138



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of	:	Customer Number: 20277
Tsukasa OOISHI	:	Confirmation Number: 5634
Application No.: 10/777,069	:	Group Art Unit: 2824
Filed: February 13, 2004	:	Examiner: NGUYEN, VAN THU T

For: THIN FILM MAGNETIC MEMORY DEVICE FOR WRITING DATA OF A PLURALITY OF BITS IN PARALLEL

INFORMATION DISCLOSURE STATEMENT

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

Each non-English language reference was first cited in a corresponding foreign application search report or office action and its relevance discussed therein. A copy of the

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foreign search report or office action, together with an English language version thereof, is attached for the Examiner's information.

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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**Please recognize our Customer No. 20277
as our correspondence address.**

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

 ATTY. DOCKET NO.
067161-0138

 SERIAL NO.
10/777,069

 APPLICANT
Tsukasa OOISHI

 FILING DATE
February 13, 2004

 GROUP
2824

(PTO-1449)

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US 6,608,776 B2	08/19/2003	Hidaka	Counterpart of DE 101 23 332
		US 2004/0047196 A1	03/11/2004	Hidaka	Counterpart of DE 101 23 332
		US 6,778,430 B2	08/17/2004	Hidaka	Counterpart of DE 101 33 646 A1
		US 5,894,447	04/13/1999	Takashima	Counterpart of JP 10-106255
		US 5,732,016	03/24/1998	Chen et al.	Counterpart of DE 197 26 077 A1
		US 5,920,500	07/06/1999	Tehrani et al.	Counterpart of DE 197 26 852 A1
		US 5,946,227	08/31/1999	Naji	
		US 5,448,515	09/05/1995	Fukami et al.	
		US 5,734,606	03/31/1998	Tehrani et al.	

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes -Number 4 -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes No	
		DE 101 23 332	11/28/2002	mitsubishi denki k.k.	Counterpart of USP 6,608,776 B2 & USP 2004/0047196 A1		X
		DE 101 33 646 A1	04/18/2002	mitsubishi denki k.k.	Counterpart of USP 6,778,430 B2		X
		JP 10-106255	04/24/1998	TOSHIBA CORP	Counterpart of USP 5,894,447	JAPAN (w/English Abstract)	
		DE 197 26 077 A1	01/08/1998	MOTOROLA, INC	Counterpart of USP 5,732,016		X
		DE 197 26 852 A1	02/26/1998	MOTOROLA, INC	Counterpart of USP 5,920,500		X
		EP 0 507 451 A2	10/07/1992	mitsubishi denki kabushiki		x	

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		Durlam, M. et al., "Nonvolatile RAM based on magnetic tunnel junction elements" IEEE International Solid-State Circuits Conference, 7 to 9 February 2000, pp. 130-131.
		Scheuerlein, R. et al., "A 10ns read and write nonvolatile memory array using a magnetic tunnel junction and FET switch in each cell" IEEE International Solid-State Circuits Conference, 7 to 9 February 2000, pp. 128-129.

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.